IRF730
Rev.H Jul.-2018

DATA SHEET

/ Descriptions

TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

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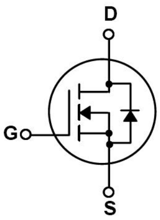
Low gate charge, low crss, fast switching.

/ Applications

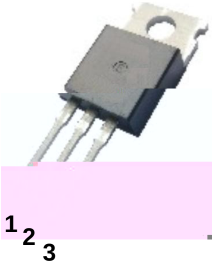
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



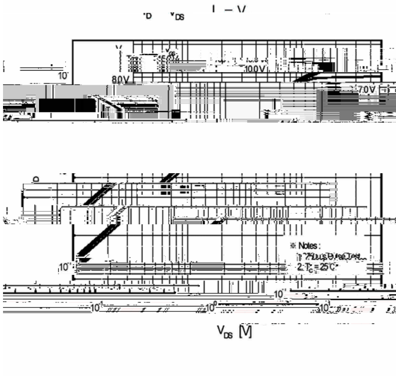
PIN1 G PIN 2 D PIN 3 S

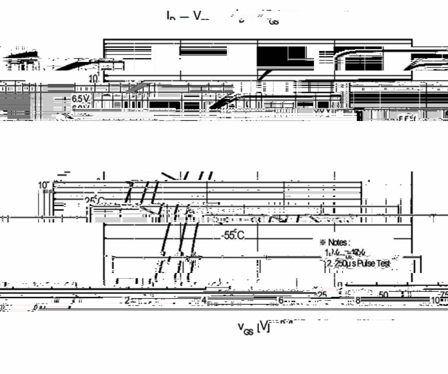
/ h_{FE} Classifications & Marking

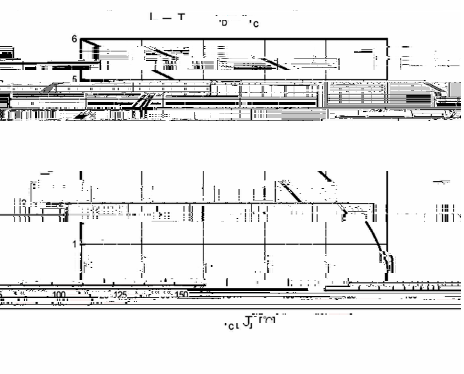
See Marking Instructions.

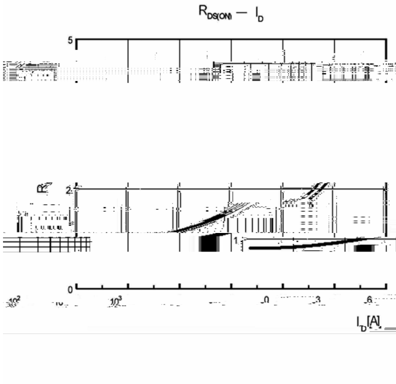
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	400	V
Drain Current	I_D(Tc=25)	6.0	A
	I_D(Tc=100)	3.6	A
Pulsed Drain Current	I_{DM}	24	A
Gate-Source Voltage	V_{GSS}	±30	V
Avalanche Current	I_{AR}	5.5	A
Single Pulsed Avalanche Energy	E_{AS}	390	mJ
Repetitive Avalanche Energy	E_{AR}	8.75	mJ
Total Power Dissipation	P_D(Tc=25)	87.5	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 150	R

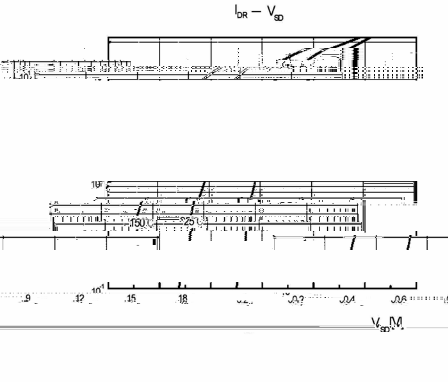
/ Electrical Characteristic Curve

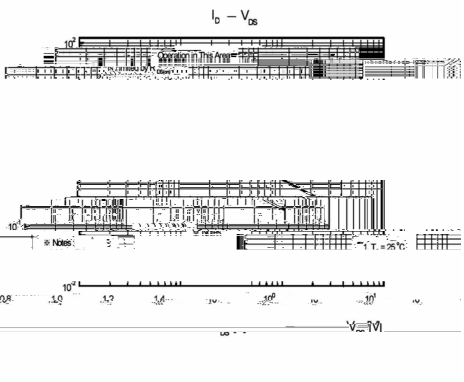


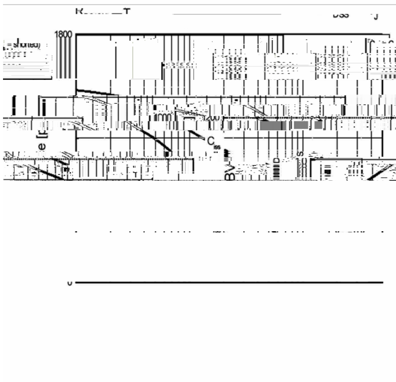


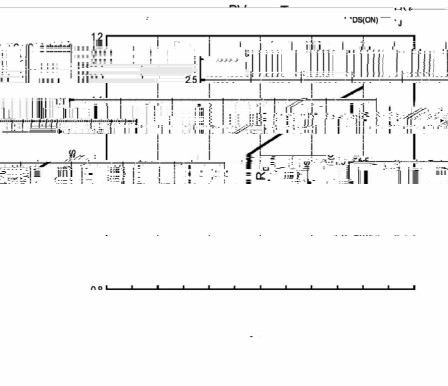


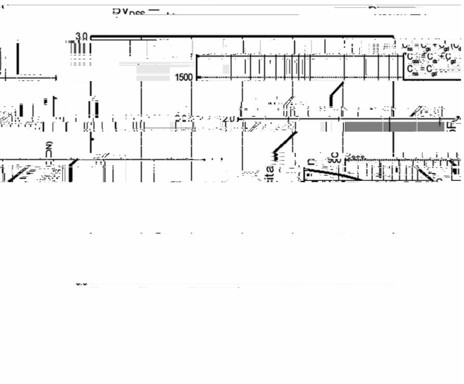








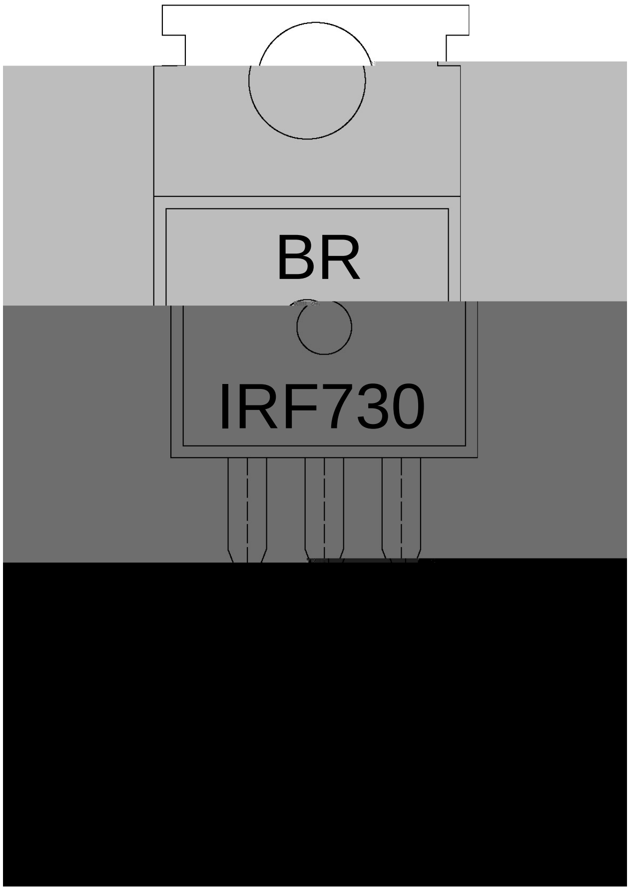




/ Package Dimensions

Symbol	Dimensions In Millimeters Min	Max	Symbol	Dimensions In Millimeters Min	Max
A	9.8	10.2	C	1.2	1.4
B	3.56	3.64	D	6.3	6.7
[illegible]	15.7	16.1	B1	9.0	9.4
[illegible]	2.6	3.61	[illegible]	2.2	2.6
[illegible]	8.6	10.6	[illegible]	0.7	0.9
[illegible]	[illegible]	[illegible]	[illegible]	[illegible]	[illegible]
[illegible]	[illegible]	[illegible]	[illegible]	[illegible]	[illegible]
[illegible]	1.45	[illegible]	[illegible]	0.2	1.25

/ Marking Instructions



BR

IRF730

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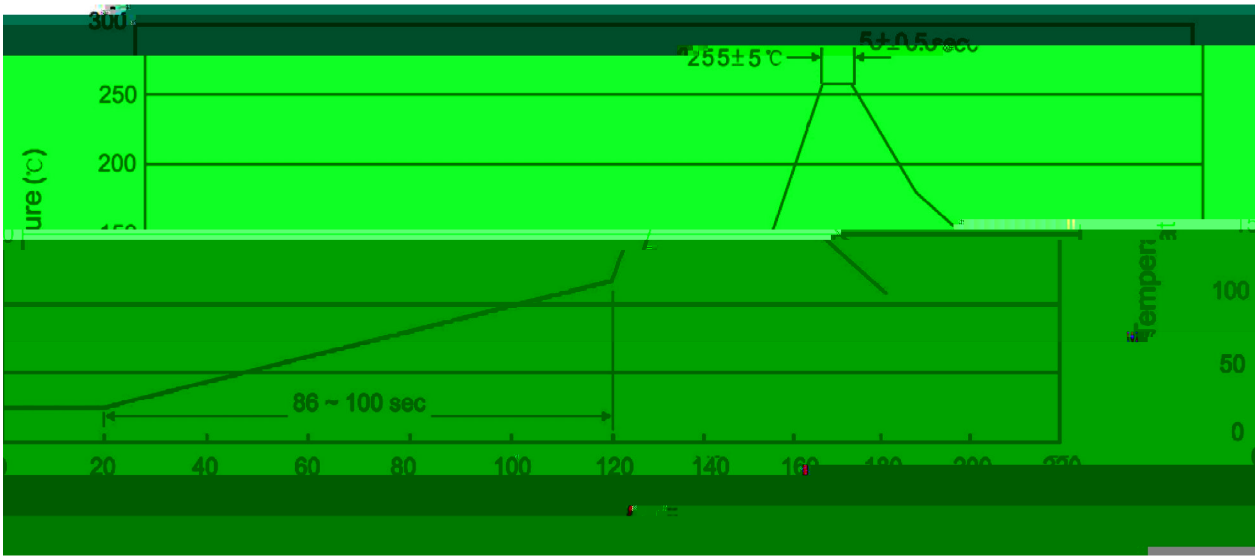
Note:

BR:	Company Code
IRF730:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1 25 150 60 90sec;
1.Preheating:25~150 , Time:60~90sec.

2 255±5 5±0.5sec;
2.Peak Temp.:255±5 , Duration:5±0.5sec.

3 2 10 /sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type